

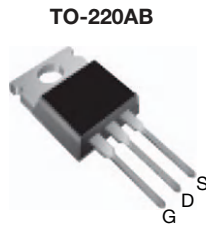
## TSM9NB50-VB Datasheet

### N-Channel 500V (D-S)Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	500	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.660
$Q_g$ (Max.) (nC)	81	
$Q_{gs}$ (nC)	20	
$Q_{gd}$ (nC)	36	
Configuration	Single	

#### FEATURES

- Lower Gate Charge  $Q_g$  Results in Simpler Drive Requirements
- Improved Gate, Avalanche and Dynamic  $dV/dt$  Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage
- Compliant to RoHS Directive 2002/95/EC



ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	500	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current	$V_{GS}$ at 10 V	$T_C = 25\text{ }^\circ\text{C}$	13	A
		$T_C = 100\text{ }^\circ\text{C}$	8.1	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	50		
Linear Derating Factor		2.0	W/ $^\circ\text{C}$	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	560	mJ	
Avalanche Current <sup>a</sup>	$I_{AR}$	13	A	
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$	25	mJ	
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	250	W
Peak Diode Recovery $dV/dt$ <sup>c</sup>	$dV/dt$	9.2	V/ns	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 150	$^\circ\text{C}$	
Soldering Recommendations (Peak Temperature)	for 10 s	300 <sup>d</sup>		
Mounting Torque	6-32 or M3 screw	10		lbf · in
		1.1	N · m	

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 5.7\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 14\text{ A}$ ,  $dV/dt = 7.6\text{ V/ns}$  (see fig. 12a).
- $I_{SD} \leq 14\text{ A}$ ,  $dI/dt \leq 250\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greasd Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.50	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT		
<b>Static</b>									
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	-	V		
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	0.55	-	V/°C		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V		
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA		
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	$\mu\text{A}$		
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250			
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 8.4\text{ A}^b$	-	0.660	-	$\Omega$		
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 8.4\text{ A}$		8.1	-	-	S		
<b>Dynamic</b>									
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5		-	1910	-	pF		
Output Capacitance	$C_{oss}$			-	290	-			
Reverse Transfer Capacitance	$C_{rss}$			-	11	-			
Output Capacitance	$C_{oss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	2730	-	pF		
			$V_{DS} = 400\text{ V}, f = 1.0\text{ MHz}$	-	82	-			
Effective Output Capacitance	$C_{oss\text{ eff.}}$	$V_{DS} = 0\text{ V to } 400\text{ V}^c$		-	160	-			
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$		-	-	81	nC		
Gate-Source Charge	$Q_{gs}$			$I_D = 14\text{ A}, V_{DS} = 400\text{ V}$ , see fig. 6 and 13 <sup>b</sup>		-		-	20
Gate-Drain Charge	$Q_{gd}$					-		-	36
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}$		-	15	-	ns		
Rise Time	$t_r$			$V_{DD} = 250\text{ V}, I_D = 14\text{ A}, R_g = 7.5\text{ }\Omega$ , see fig. 10 <sup>b</sup>		-		39	-
Turn-Off Delay Time	$t_{d(off)}$					-		39	-
Fall Time	$t_f$					-		31	-
<b>Drain-Source Body Diode Characteristics</b>									
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	13	A		
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	56			
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 14\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.5	V		
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 14\text{ A}, T_J = 125\text{ }^\circ\text{C}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	370	550	ns		
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	4.4	6.5	$\mu\text{C}$		
Body Diode Reverse Recovery Current	$I_{RRM}$			-	21	31	A		
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )							

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- c.  $C_{oss\text{ eff.}}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Fig. 1 - Typical Output Characteristics**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 2 - Typical Output Characteristics**



**Fig. 4 - Normalized On-Resistance vs. Temperature**



91095\_05

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



91095\_07

Fig. 7 - Typical Source-Drain Diode Forward Voltage



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Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



91095\_08

Fig. 8 - Maximum Safe Operating Area



Fig. 9 - Maximum Drain Current vs. Case Temperature

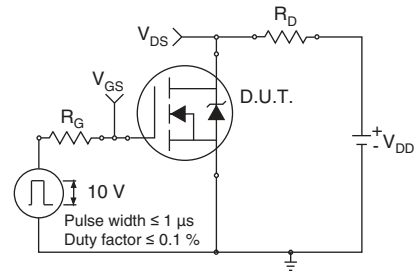


Fig. 10a - Switching Time Test Circuit

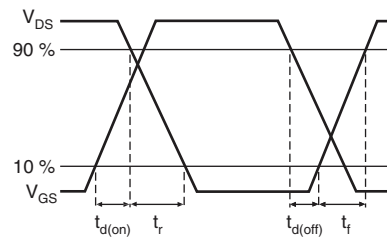


Fig. 10b - Switching Time Waveforms

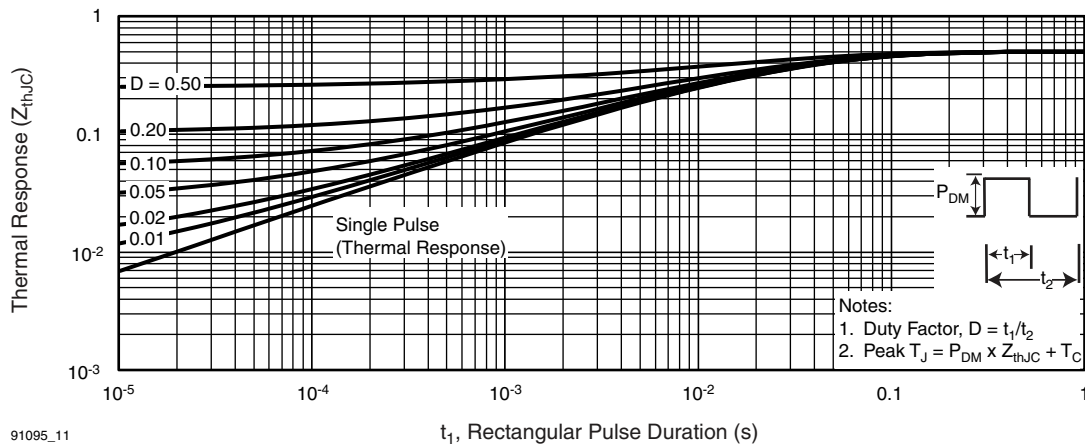


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms

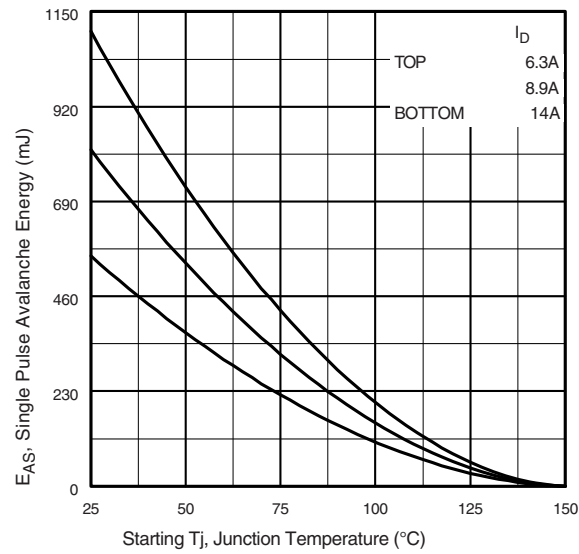


Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform

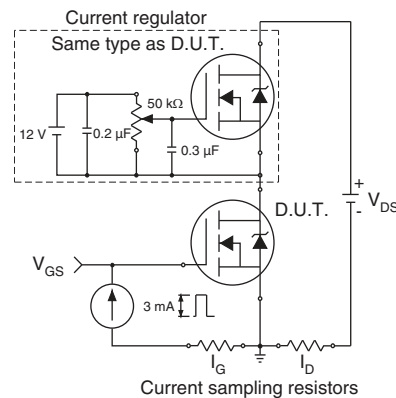


Fig. 13b - Gate Charge Test Circuit

**Peak Diode Recovery dV/dt Test Circuit**



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**





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